

# Hiroshi Yamaguchi

## List of Publications by Year in Descending Order

**Source:** <https://exaly.com/author-pdf/9000937/hiroshi-yamaguchi-publications-by-year.pdf>

**Version:** 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

286  
papers

5,898  
citations

35  
h-index

67  
g-index

327  
ext. papers

6,630  
ext. citations

3.7  
avg, IF

5.75  
L-index

#	Paper	IF	Citations
286	Development of an Optomechanical Device with Extremely Low Optical Energy Loss. <i>NTT Technical Review</i> , <b>2022</b> , 20, 49-53		
285	Fabrication of Suspended Nanowire Mechanical Devices Using Inkjet Technology. <i>NTT Technical Review</i> , <b>2022</b> , 20, 59-64		
284	New Method of Chaos Generation by Using Nanomechanical Oscillator. <i>NTT Technical Review</i> , <b>2022</b> , 20, 37-42		
283	Control of Elastic Waves Using Phonon Waveguides and Phononic Crystals. <i>NTT Technical Review</i> , <b>2022</b> , 20, 43-48		
282	On-Chip Wave Manipulations Enabled by Electromechanical Phononic-Crystal Waveguides. <i>Quantum Science and Technology</i> , <b>2022</b> , 43-72	1.2	
281	Buckling-induced quadratic nonlinearity in silicon phonon waveguide structures. <i>Japanese Journal of Applied Physics</i> , <b>2022</b> , 61, SD1025	1.4	0
280	Phonon-Electron-Nuclear Spin Hybrid Systems in an Electromechanical Resonator. <i>Quantum Science and Technology</i> , <b>2021</b> , 245-264	1.2	
279	Rare-Earth-Mediated Optomechanical System in the Reversed Dissipation Regime. <i>Physical Review Letters</i> , <b>2021</b> , 126, 047404	7.4	3
278	Mode-sensitive magnetoelastic coupling in phononic-crystal magnomechanics. <i>APL Materials</i> , <b>2021</b> , 9, 071110	5.7	0
277	Mechanical Kerr Nonlinearity of Wave Propagation in an On-Chip Nanoelectromechanical Waveguide. <i>Physical Review Applied</i> , <b>2020</b> , 13,	4.3	9
276	Real-Space Characterization of Cavity-Coupled Waveguide Systems in Hypersonic Phononic Crystals. <i>Physical Review Applied</i> , <b>2020</b> , 13,	4.3	7
275	Demonstration of Multiple Internal Resonances in a Microelectromechanical Self-Sustained Oscillator. <i>Physical Review Applied</i> , <b>2020</b> , 13,	4.3	8
274	Noise Reduction of a Mechanical Resonator by Laser Cooling. <i>Vacuum and Surface Science</i> , <b>2020</b> , 63, 536-541		
273	Near-field cavity optomechanical coupling in a compound semiconductor nanowire. <i>Communications Physics</i> , <b>2020</b> , 3,	5.4	1
272	Novel Fabrication Technique of Suspended Nanowire Devices for Nanomechanical Applications. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900401	1.3	2
271	Generic Rotating-Frame-Based Approach to Chaos Generation in Nonlinear Micro- and Nanoelectromechanical System Resonators. <i>Physical Review Letters</i> , <b>2020</b> , 125, 174301	7.4	3
270	Virtual Exceptional Points in an Electromechanical System. <i>Physical Review Applied</i> , <b>2019</b> , 11,	4.3	8

269	Pulse-width modulated oscillations in a nonlinear resonator under two-tone driving as a means for MEMS sensor readout. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SBBI05	1.4	3
268	Electron paramagnetic resonance spectroscopy using a single artificial atom. <i>Communications Physics</i> , <b>2019</b> , 2,	5.4	14
267	Limit cycles and bifurcations in a nonlinear MEMS resonator with a 1:3 internal resonance. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 103103	3.4	20
266	Electrostatically Induced Phononic Crystal. <i>Physical Review Applied</i> , <b>2019</b> , 11,	4.3	12
265	On-Chip Piezoelectric Actuation of Nanomechanical Resonators Containing a Two-Dimensional Electron Gas. <i>JETP Letters</i> , <b>2019</b> , 109, 261-265	1.2	0
264	Modal Analysis Investigation of Mechanical Kerr Frequency Combs. <i>Springer Proceedings in Physics</i> , <b>2019</b> , 141-157	0.2	0
263	On-chip temporal focusing of elastic waves in a phononic crystal waveguide. <i>Nature Communications</i> , <b>2018</b> , 9, 1331	17.4	34
262	Phonon-bottlenecked spin relaxation of Er <sup>3+</sup> :Y <sub>2</sub> SiO <sub>5</sub> at sub-kelvin temperatures. <i>Applied Physics Express</i> , <b>2018</b> , 11, 043002	2.4	7
261	Selective activation of localized mechanical resonators via a phonon waveguide. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 043104	3.4	3
260	Electron paramagnetic resonance spectroscopy of Er <sup>3+</sup> :Y <sub>2</sub> SiO <sub>5</sub> using a Josephson bifurcation amplifier: Observation of hyperfine and quadrupole structures. <i>Physical Review Materials</i> , <b>2018</b> , 2,	3.2	8
259	Dynamical coupling between a nuclear spin ensemble and electromechanical phonons. <i>Nature Communications</i> , <b>2018</b> , 9, 2993	17.4	10
258	An opto-electro-mechanical system based on evanescently-coupled optical microbottle and electromechanical resonator. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 201103	3.4	11
257	Dynamic Control of the Coupling between Dark and Bright Excitons with Vibrational Strain. <i>Physical Review Letters</i> , <b>2018</b> , 120, 267401	7.4	12
256	Feedback control of multiple mechanical modes in coupled micromechanical resonators. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 053106	3.4	5
255	Broadband reconfigurable logic gates in phonon waveguides. <i>Scientific Reports</i> , <b>2017</b> , 7, 12745	4.9	12
254	GaAs-based micro/nanomechanical resonators. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 103003	1.8	28
253	A correlated electromechanical system. <i>New Journal of Physics</i> , <b>2017</b> , 19, 033026	2.9	2
252	An electromechanical Ising Hamiltonian. <i>Science Advances</i> , <b>2016</b> , 2, e1600236	14.3	48

251	Observation of Collective Coupling between an Engineered Ensemble of Macroscopic Artificial Atoms and a Superconducting Resonator. <i>Physical Review Letters</i> , <b>2016</b> , 117, 210503	7.4	50
250	Gate-controlled electromechanical backaction induced by a quantum dot. <i>Nature Communications</i> , <b>2016</b> , 7, 11132	17.4	40
249	A strict experimental test of macroscopic realism in a superconducting flux qubit. <i>Nature Communications</i> , <b>2016</b> , 7, 13253	17.4	73
248	An electromechanical displacement transducer. <i>Applied Physics Express</i> , <b>2016</b> , 9, 086701	2.4	1
247	Energy Dissipation in Graphene Mechanical Resonators with and without Free Edges. <i>Micromachines</i> , <b>2016</b> , 7,	3.3	8
246	Hopf and period-doubling bifurcations in an electromechanical resonator. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 073101	3.4	21
245	Enhanced visibility of two-mode thermal squeezed states via degenerate parametric amplification and resonance. <i>New Journal of Physics</i> , <b>2016</b> , 18, 083009	2.9	5
244	Electron paramagnetic resonance spectroscopy using a direct current-SQUID magnetometer directly coupled to an electron spin ensemble. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 052601	3.4	14
243	A strongly coupled E-type micromechanical system. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 153105	3.4	16
242	Optically detected magnetic resonance of high-density ensemble of NV centers in diamond. <i>Journal of Physics Condensed Matter</i> , <b>2016</b> , 28, 275302	1.8	23
241	Dispersive and dissipative coupling in a micromechanical resonator embedded with a nanomechanical resonator. <i>Nano Letters</i> , <b>2015</b> , 15, 2312-7	11.5	31
240	Renovation of three-dimensional electron beam lithography for improvement of positioning accuracy and reduction of turnaround time. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 06FD02	1.4	1
239	Improving the lifetime of the nitrogen-vacancy-center ensemble coupled with a superconducting flux qubit by applying magnetic fields. <i>Physical Review A</i> , <b>2015</b> , 91,	2.6	17
238	Improving the coherence time of a quantum system via a coupling to a short-lived system. <i>Physical Review Letters</i> , <b>2015</b> , 114, 120501	7.4	20
237	Analysis of the spectroscopy of a hybrid system composed of a superconducting flux qubit and diamond NV(-) centers. <i>Journal of Physics Condensed Matter</i> , <b>2015</b> , 27, 345702	1.8	0
236	Observing the semiconducting band-gap alignment of MoS2 layers of different atomic thicknesses using a MoS2/SiO2/Si heterojunction tunnel diode. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 053101	3.4	7
235	Cavity-less on-chip optomechanics using excitonic transitions in semiconductor heterostructures. <i>Nature Communications</i> , <b>2015</b> , 6, 8478	17.4	20
234	High-Temperature Operation of Electrostatically-Excited Single-Crystalline 4H-SiC Microcantilever Resonators. <i>Materials Science Forum</i> , <b>2015</b> , 821-823, 914-918	0.4	

233	Scalable quantum computation architecture using always-on Ising interactions via quantum feedforward. <i>Physical Review A</i> , <b>2015</b> , 91,	2.6	2
232	Proposed Robust Entanglement-Based Magnetic Field Sensor Beyond the Standard Quantum Limit. <i>Physical Review Letters</i> , <b>2015</b> , 115, 170801	7.4	35
231	Optically induced strong intermodal coupling in mechanical resonators at room temperature. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 091906	3.4	3
230	Phonon propagation dynamics in band-engineered one-dimensional phononic crystal waveguides. <i>New Journal of Physics</i> , <b>2015</b> , 17, 113032	2.9	15
229	Direct fabrication of a W-C SNS Josephson junction using focused-ion-beam chemical vapour deposition. <i>Journal of Micromechanics and Microengineering</i> , <b>2014</b> , 24, 055015	2	5
228	Phonon waveguides for electromechanical circuits. <i>Nature Nanotechnology</i> , <b>2014</b> , 9, 520-4	28.7	78
227	Nonlinear electromechanical resonators ~ from phonon lasing operation to nanomechanical processors <b>2014</b> ,		1
226	A multimode electromechanical parametric resonator array. <i>Scientific Reports</i> , <b>2014</b> , 4, 4448	4.9	44
225	Mechanical random access memory in a phonon circuit. <i>Applied Physics Express</i> , <b>2014</b> , 7, 125201	2.4	12
224	Rapid switching in high-Q mechanical resonators. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 083114	3.4	15
223	Nonlinear optical spectra having characteristics of Fano interferences in coherently coupled lowest exciton biexciton states in semiconductor quantum dots. <i>AIP Advances</i> , <b>2014</b> , 4, 107124	1.5	
222	Entangled-state generation and Bell inequality violations in nanomechanical resonators. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	28
221	Two-mode thermal-noise squeezing in an electromechanical resonator. <i>Physical Review Letters</i> , <b>2014</b> , 113, 167203	7.4	58
220	Energy dissipation in edged and edgeless graphene mechanical resonators. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 064304	2.5	8
219	Stability and Reactivity of [11-20] Step in Initial Stage of Epitaxial Graphene Growth on SiC(0001). <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 1150-1153	0.4	
218	Fabrication of Electrostatically Actuated 4H-SiC Microcantilever Resonators by Using n/p/n Epitaxial Structures and Doping-Selective Electrochemical Etching. <i>Materials Science Forum</i> , <b>2014</b> , 778-780, 780-783	0.4	1
217	Coherent phonon manipulation in coupled mechanical resonators. <i>Nature Physics</i> , <b>2013</b> , 9, 480-484	16.2	202
216	Graphene-Based Nano-Electro-Mechanical Switch with High On/Off Ratio. <i>Applied Physics Express</i> , <b>2013</b> , 6, 055101	2.4	21

215	Single-crystalline 4H-SiC micro cantilevers with a high quality factor. <i>Sensors and Actuators A: Physical</i> , <b>2013</b> , 197, 122-125	3.9	14
214	Phonon lasing in an electromechanical resonator. <i>Physical Review Letters</i> , <b>2013</b> , 110, 127202	7.4	101
213	Ferromagnetic-induced component in piezoresistance of GaMnAs. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	8
212	Self-sustained oscillations of a torsional SQUID resonator induced by Lorentz-force back-action. <i>Nature Communications</i> , <b>2013</b> , 4, 1803	17.4	16
211	A phonon transistor in an electromechanical resonator array. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 213102	3.4	26
210	Superconductivity in Tungsten-Carbide Nanowires Deposited from the Mixtures of W(CO) <sub>6</sub> and C <sub>14</sub> H <sub>10</sub> . <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 075001	1.4	8
209	Universal three-dimensional nanofabrication for hard materials. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2013</b> , 31, 051802	1.3	1
208	Parametric mode mixing in asymmetric doubly clamped beam resonators. <i>New Journal of Physics</i> , <b>2013</b> , 15, 015023	2.9	17
207	Ultrahigh-Q Micromechanical Resonators by Using Epitaxially Induced Tensile Strain in GaNAs. <i>Applied Physics Express</i> , <b>2013</b> , 6, 111201	2.4	8
206	Epitaxial Trilayer Graphene Mechanical Resonators Obtained by Electrochemical Etching Combined with Hydrogen Intercalation. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 04CH01	1.4	11
205	Direct Biexciton Creation with Two-Photon Excitation for Ideal Entangled Photon Pair Emissions in Optically Active Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 120202	1.4	2
204	Modifying exciton optical properties in quantum dots with coherent phonons induced by ultrafast optical pulses. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 112104	3.4	3
203	Multi-mode parametric coupling in an electromechanical resonator. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 153105	3.4	21
202	Quantum point contact displacement transducer for a mechanical resonator at sub-Kelvin temperatures. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 192105	3.4	20
201	Wide-bandwidth charge sensitivity with a radio-frequency field-effect transistor. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 143102	3.4	6
200	Stability and reactivity of steps in the initial stage of graphene growth on the SiC(0001) surface. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	15
199	Mechanical vibration of a cylindrically rolled-up cantilever shell in microelectromechanical and nanoelectromechanical systems. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	3
198	Electrical characteristics of in-plane gate logic devices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2012</b> , 9, 385-388		1

197	Phonon-cavity electromechanics. <i>Nature Physics</i> , <b>2012</b> , 8, 387-392	16.2	99
196	Electron beam lithography on vertical side faces of micrometer-order Si block. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 041601	1.3	6
195	An electromechanical membrane resonator. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 063102	3.4	29
194	Spatially modulated photoluminescence properties in dynamically strained GaAs/AlAs quantum wells by surface acoustic wave. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 162109	3.4	6
193	Dynamic control of photoluminescence polarization properties in GaAs/AlAs quantum wells by surface acoustic waves. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	2
192	Tuneable electromechanical comb generation. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 113109	3.4	6
191	Motion detection of a micromechanical cantilever through magneto-piezovoltage in two-dimensional electron systems. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 012106	3.4	4
190	Optomechanical photoabsorption spectroscopy of exciton states in GaAs. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 082107	3.4	6
189	Charged exciton creation with two-color optical excitation method and analysis of initialization process of electron spin qubit in quantum dots. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 123520	2.5	2
188	Coherent Control of Micro/Nanomechanical Oscillation Using Parametric Mode Mixing. <i>Applied Physics Express</i> , <b>2012</b> , 5, 014001	2.4	14
187	Microscopic Raman Mapping of Epitaxial Graphene on 4H-SiC(0001). <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 06FD06	1.4	5
186	Wide-band idler generation in a GaAs electromechanical resonator. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	18
185	dc SQUIDS as linear displacement detectors for embedded micromechanical resonators. <i>Comptes Rendus Physique</i> , <b>2011</b> , 12, 817-825	1.4	1
184	Discrete-time quadrature feedback cooling of a radio-frequency mechanical resonator. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 013113	3.4	10
183	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 070115	1.4	8
182	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 095601	1.4	7
181	Operating principle and integration of in-plane gate logic devices. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 242106	3.4	6
180	Carrier-mediated optomechanical coupling in GaAs cantilevers. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	5



179	Creation of charged excitons with two-color excitation method and initialization of electron spin qubit in quantum dots. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 032101	3.4	4
178	High-sensitivity charge detection using antisymmetric vibration in coupled micromechanical oscillators. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 014103	3.4	24
177	Vibration amplification, damping, and self-oscillations in micromechanical resonators induced by optomechanical coupling through carrier excitation. <i>Physical Review Letters</i> , <b>2011</b> , 106, 036801	7.4	42
176	Electromechanical Displacement Detection With an On-Chip High Electron Mobility Transistor Amplifier. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 06GJ01	1.4	1
175	Interconnect-free parallel logic circuits in a single mechanical resonator. <i>Nature Communications</i> , <b>2011</b> , 2, 198	17.4	110
174	Remote actuation of a mechanical resonator. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 103105	3.4	
173	Electromechanical Displacement Detection With an On-Chip High Electron Mobility Transistor Amplifier. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 06GJ01	1.4	2
172	Theoretical Study on Magnetoelectric and Thermoelectric Properties for Graphene Devices. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 070115	1.4	8
171	Theoretical Study on Epitaxial Graphene Growth by Si Sublimation from SiC(0001) Surface. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 095601	1.4	8
170	Atomic Structure and Physical Properties of Epitaxial Graphene Islands Embedded in SiC(0001) Surfaces. <i>Applied Physics Express</i> , <b>2010</b> , 3, 115103	2.4	9
169	A symmetry-breaking electromechanical detector. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 213103	3.4	12
168	Tunable backaction of a DC SQUID on an integrated micromechanical resonator. <i>Physical Review Letters</i> , <b>2010</b> , 105, 207203	7.4	27
167	Enhanced force sensitivity and noise squeezing in an electromechanical resonator coupled to a nanotransistor. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 253105	3.4	13
166	Feedback Cooling of a Strained GaAs Micromechanical Beam Resonator. <i>Applied Physics Express</i> , <b>2010</b> , 3, 065201	2.4	6
165	Contact Conductance Measurement of Locally Suspended Graphene on SiC. <i>Applied Physics Express</i> , <b>2010</b> , 3, 045101	2.4	17
164	Tunable coupling of mechanical vibration in GaAs micro-resonators. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2010</b> , 42, 2849-2852	3	6
163	Resist Coating on Vertical Side Faces Using Conventional Spin Coating for Creating Three-Dimensional Nanostructures in Semiconductors. <i>Applied Physics Express</i> , <b>2010</b> , 3, 106501	2.4	6
162	Controlling Quality Factor in Micromechanical Resonators by Carrier Excitation. <i>Applied Physics Express</i> , <b>2009</b> , 2, 035001	2.4	5



161	Magneto-optical spectroscopy of excitons and trions in charge-tunable quantum dots. <i>Physical Review B</i> , <b>2009</b> , 79,	3.3	11
160	Room temperature piezoelectric displacement detection via a silicon field effect transistor. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 233102	3.4	11
159	Photoluminescence dynamics in GaAs/AlAs quantum wells modulated by one-dimensional standing surface acoustic waves. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 131912	3.4	6
158	Optical Tuning of Coupled Micromechanical Resonators. <i>Applied Physics Express</i> , <b>2009</b> , 2, 062202	2.4	32
157	Local conductance measurements of double-layer graphene on SiC substrate. <i>Nanotechnology</i> , <b>2009</b> , 20, 445704	3.4	36
156	ELECTRON SPIN IMAGING IN QUANTUM HALL DEVICES BY KERR ROTATION MEASUREMENT. <i>International Journal of Modern Physics B</i> , <b>2009</b> , 23, 2750-2754	1.1	
155	OPTICALLY INDUCED DYNAMIC NUCLEAR SPIN POLARIZATION IN QUANTUM HALL REGIME OBSERVED BY A TIME-RESOLVED KERR ROTATION. <i>International Journal of Modern Physics B</i> , <b>2009</b> , 23, 2755-2759	1.1	1
154	Direct Actuation of GaAs Membrane with the Microprobe of Scanning Probe Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 06FG06	1.4	1
153	Evaluation of Thermal/Mechanical Vibration Amplitude and Mechanical Properties of Carbon Nanopillars Using Scanning Electron Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 06FG07	1.4	4
152	Theoretical Study of Epitaxial Graphene Growth on SiC(0001) Surfaces. <i>Applied Physics Express</i> , <b>2009</b> , 2, 065502	2.4	59
151	Stacking domains of epitaxial few-layer graphene on SiC(0001). <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	74
150	Spatial and temporal modulation of exciton photoluminescence properties in GaAs/AlAs dynamic quantum dots formed by surface acoustic waves. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	9
149	Bit storage and bit flip operations in an electromechanical oscillator. <i>Nature Nanotechnology</i> , <b>2008</b> , 3, 275-9	28.7	208
148	Motion detection of a micromechanical resonator embedded in a d.c. SQUID. <i>Nature Physics</i> , <b>2008</b> , 4, 785-788	16.2	146
147	Three-dimensional alignment with 10nm order accuracy in electron-beam lithography on rotated sample for three-dimensional nanofabrication. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2008</b> , 26, 2529-2533 <sup>9</sup>		
146	Thermoelastic damping in GaAs micromechanical resonators. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 2920-2922		10
145	In-plane conductance measurement of graphene nanoislands using an integrated nanogap probe. <i>Nanotechnology</i> , <b>2008</b> , 19, 495701	3.4	20
144	Microscopic thickness determination of thin graphite films formed on SiC from quantized oscillation in reflectivity of low-energy electrons. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	301

143	Single-Electron-Resolution Electrometer Based on Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 8305-8310	1.4	28
142	Cooling of a micro-mechanical resonator by the back-action of Lorentz force. <i>New Journal of Physics</i> , <b>2008</b> , 10, 043015	2.9	27
141	Height Dependence of Young's Modulus for Carbon Nanopillars Grown by Focused-Ion-Beam-Induced Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 5116-5119	1.4	7
140	Low-Energy Electron Emission from an Electron Inversion Layer of a Si/SiO <sub>2</sub> /Si Cathode for Nano-Decomposition. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 5106-5108	1.4	1
139	Parametrically pumped ultrahigh Q electromechanical resonator. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 253109	3.4	21
138	Piezoelectrically pumped parametric amplification and Q enhancement in an electromechanical oscillator. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 173109	3.4	37
137	Improved resonance characteristics of GaAs beam resonators by epitaxially induced strain. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 251913	3.4	29
136	Electron-spin manipulation and resonator readout in a double-quantum-dot nanoelectromechanical system. <i>Physical Review Letters</i> , <b>2008</b> , 100, 136802	7.4	17
135	Spin dynamics of two-dimensional electrons in a quantum Hall system probed by time-resolved Kerr rotation spectroscopy. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	24
134	Flexible Nanofabrication in Three-Dimensional Electron-Beam Lithography Enhanced by Suppression of Proximity Effect. <i>Applied Physics Express</i> , <b>2008</b> , 1, 097001	2.4	9
133	Local conductance measurement of few-layer graphene on SiC substrate using an integrated nanogap probe. <i>Journal of Physics: Conference Series</i> , <b>2008</b> , 100, 052006	0.3	7
132	Thickness Determination of Graphene Layers Formed on SiC Using Low-Energy Electron Microscopy. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2008</b> , 6, 107-110	0.7	41
131	Spin selective optical excitation in charge-tunable GaAs quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 2904-2906		1
130	Mechanically detected field-induced Mn spin rotation in GaMnAs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 2893-2895		
129	Two-Dimensional Patterning of Flexible Designs with High Half-Pitch Resolution by Using Block Copolymer Lithography. <i>Advanced Materials</i> , <b>2008</b> , 20, 1684-1689	2.4	26
128	Magnetic field induced by the carbon nanotubes current by magnetic force microscopy. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 2220-2221	3	4
127	Piezoresistance of suspended InAs/AlGaSb heterostructure nanobeam. <i>Journal of Crystal Growth</i> , <b>2007</b> , 301-302, 897-901	1.6	1
126	Magnetization of free standing GaMnAs. <i>Journal of Crystal Growth</i> , <b>2007</b> , 308, 204-207	1.6	1

125	Semiconductor heterostructure studies using emerging technologies. <i>Physica Status Solidi (B): Basic Research</i> , <b>2007</b> , 244, 2988-3001	1.3	2
124	A $\delta$ -Doped InGaP/InGaAs pHEMT With Different Doping Profiles for Device-Linearity Improvement. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 1617-1625	2.9	16
123	Field-Effect Transistor with Deposited Graphite Thin Film. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 2615-2617	1.4	4
122	Controllable coupling between flux qubit and nanomechanical resonator by magnetic field. <i>New Journal of Physics</i> , <b>2007</b> , 9, 35-35	2.9	64
121	Giant Magneto-Piezoresistance and Internal Friction in a Two-Dimensional Electron System. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L658-L660	1.4	4
120	Modulation of Young's Modulus of Poly(methyl methacrylate) Nanobeam Due to Electron-Beam Exposure. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L1225-L1227	1.4	6
119	Local Conductance Imaging of Semiconductor Nanowires on an Insulative Substrate Using an Integrated Nanogap Probe. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 5639-5642	1.4	4
118	Infrared detection with silicon nano-field-effect transistors. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 223108	3.4	13
117	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 102106	3.4	77
116	Impact of space-energy correlation on variable range hopping in a transistor. <i>Physical Review Letters</i> , <b>2007</b> , 98, 166601	7.4	4
115	Growth of very-high-mobility AlGaSb/InAs high-electron-mobility transistor structure on si substrate for high speed electronic applications. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 023509	3.4	18
114	Photoluminescence Dynamics of GaAs/AlAs Quantum Wells Modulated by Surface Acoustic Waves. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, L758-L760	1.4	8
113	Pattern Transfer of Laterally Aligned Lamellar Domains of Diblock Copolymers. <i>Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]</i> , <b>2007</b> , 20, 767-769	0.7	2
112	Nanogap electrodes on Si cantilever for local conductance measurement. <i>Journal of Physics: Conference Series</i> , <b>2007</b> , 61, 856-860	0.3	10
111	Transfer and Detection of Single Electrons Using Metal-Oxide-Semiconductor Field-Effect Transistors. <i>IEICE Transactions on Electronics</i> , <b>2007</b> , E90-C, 943-948	0.4	2
110	Carbon Multiprobe on a Si Cantilever for Pseudo-Metal/Oxide/Semiconductor Field-Effect-Transistor. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, 2009-2013	1.4	8
109	Electron phase modulation in a suspended InAs/AlGaSb nanomechanical beam. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 192106	3.4	4
108	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and 295K. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	13

107	Device linearity comparison of uniformly doped and $\delta$ -doped In <sub>0.52</sub> Al <sub>0.48</sub> As/In <sub>0.6</sub> Ga <sub>0.4</sub> As metamorphic HEMTs. <i>IEEE Electron Device Letters</i> , <b>2006</b> , 27, 535-537	4.4	12
106	Corrections to Device Linearity Comparison of Uniformly Doped and $\delta$ -Doped In <sub>0.52</sub> Al <sub>0.48</sub> As/hIn <sub>0.6</sub> Ga <sub>0.4</sub> As Metamorphic HEMTs <i>IEEE Electron Device Letters</i> , <b>2006</b> , 27, 866-866	4.4	
105	Proposal of Carbon Nanotube Inductors. <i>Journal of Physics: Conference Series</i> , <b>2006</b> , 38, 49-52	0.3	8
104	Micromechanical Quantum Electron Transport. <i>Journal of Physics: Conference Series</i> , <b>2006</b> , 38, 152-157	0.3	1
103	Resist-Pattern Guided Self-assembly of Symmetric Diblock Copolymer. <i>Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi]</i> , <b>2006</b> , 19, 385-388	0.7	12
102	Giant magnetopiezoresistance at the localized-extended electronic state transition in a high-mobility 2DEG system. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 663-666		1
101	Enhanced emission of single quantum dot formed by interface fluctuations in photonic-crystal microcavities. <i>Photonics and Nanostructures - Fundamentals and Applications</i> , <b>2006</b> , 4, 89-93	2.6	
100	A piezoresistive cantilever integrating an InAs-based semiconductor/superconductor junction. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2006</b> , 32, 512-515	3	1
99	Force/displacement detection using quantum transport in InAs/AlGaSb two-dimensional heterostructures. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 052106	3.4	16
98	Imaging of Local Tunneling Barrier Height of InAs Nanostructures Using Low-Temperature Scanning Tunneling Microscopy. <i>AIP Conference Proceedings</i> , <b>2005</b> ,	0	1
97	Difference in Self-Assembling Morphology of Peptide Nanorings. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, 8240-8248	1.4	5
96	From ferro- to antiferromagnetism via exchange-striction of MnAs/GaAs(001). <i>Europhysics Letters</i> , <b>2005</b> , 72, 479-485	1.6	23
95	Strongly Enhanced Sensitivity of Piezoresistive Cantilevers by Utilizing the Superconducting Proximity Effect. <i>Japanese Journal of Applied Physics</i> , <b>2005</b> , 44, L893-L895	1.4	7
94	InAs-based Micromechanical Two-dimensional Electron Systems. <i>AIP Conference Proceedings</i> , <b>2005</b> ,	0	1
93	Nonequilibrium transport of InAs/GaAs(111)A heterostructures coupled with superconducting Nb electrodes. <i>Semiconductor Science and Technology</i> , <b>2004</b> , 19, S182-S184	1.8	3
92	Quantum interference effects in the magnetopiezoresistance of InAs/AlGaSb quasi-one-dimensional electron systems. <i>Physical Review Letters</i> , <b>2004</b> , 93, 036603	7.4	11
91	InAs/AlGaSb Piezoresistive Cantilever for Sub-Angstrom Scale Displacement Detection. <i>Japanese Journal of Applied Physics</i> , <b>2004</b> , 43, L424-L426	1.4	3
90	Quantum-mechanical displacement sensing using InAs/AlGaSb micromechanical cantilevers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 1053-1056	3	4

89	InAs/GaAs (111)A heteroepitaxial systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 23, 285-292	3	7
88	Piezoresistive cantilevers using InAs-based 2D Heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 24, 70-73	3	2
87	Mechanical and piezoresistive properties of InAs/AlGaSb cantilevers. <i>Applied Surface Science</i> , <b>2004</b> , 237, 645-649	6.7	4
86	Perpendicular magnetic fields in cantilever beam magnetometry. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 2773-2778	2.5	6
85	Magnetoelastic coupling of MnAs/GaAs(001) close to the phase transition. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	12
84	InAs/AlGaSb heterostructure displacement sensors for MEMS/NEMS applications. <i>Journal of Crystal Growth</i> , <b>2003</b> , 251, 556-559	1.6	6
83	Application of multi-step formation during molecular beam epitaxy for fabricating novel nanomechanical structures. <i>Journal of Crystal Growth</i> , <b>2003</b> , 251, 281-284	1.6	
82	Fabrication and characterization of novel semiconductor nanomechanical structures. <i>Surface Science</i> , <b>2003</b> , 532-535, 1171-1176	1.8	1
81	Single-Turn GaAs/InAs Nanotubes Fabricated Using the Supercritical CO <sub>2</sub> Drying Technique. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L791-L794	1.4	34
80	Microelectromechanical displacement sensing using InAs/AlGaSb heterostructures. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 394-396	3.4	22
79	Fabrication and elastic properties of InAs freestanding structures based on InAs/GaAs(111)A heteroepitaxial systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 1163-1167	3	7
78	First principles and macroscopic theories of semiconductor epitaxial growth. <i>Journal of Crystal Growth</i> , <b>2002</b> , 237-239, 206-211	1.6	14
77	Fabrication of conductive single-crystal semiconductor nanoscale electromechanical structures. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 4428-4430	3.4	12
76	Application of InAs Freestanding Membranes to Electromechanical Systems. <i>Japanese Journal of Applied Physics</i> , <b>2002</b> , 41, 2519-2521	1.4	3
75	Imaging of Zero-Dimensional States in Semiconductor Nanostructures Using Scanning Tunneling Microscopy. <i>Lecture Notes in Physics</i> , <b>2002</b> , 263-268	0.8	
74	Excellent electric properties of free-standing InAs membranes. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2372-2374	3.4	26
73	Imaging of Friedel oscillation patterns of two-dimensionally accumulated electrons at epitaxially grown InAs(111) A surfaces. <i>Physical Review Letters</i> , <b>2001</b> , 86, 3384-7	7.4	102
72	Local density of states in zero-dimensional semiconductor structures. <i>Physical Review Letters</i> , <b>2001</b> , 87, 196804	7.4	37

71	Imaging of Friedel oscillations at epitaxially grown InAs(111) A surfaces using scanning tunneling microscopy. <i>Springer Proceedings in Physics</i> , <b>2001</b> , 427-430	0.2	
70	Electron and Hole Proximity Effects in the InAs/AlSb/GaSb System. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 2448-2451	1.4	8
69	Two-dimensional growth of InSb thin films on GaAs(111)A substrates. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 589-591	3.4	54
68	Superconductor-semiconductor-superconductor junctions using NbN. <i>Superconductor Science and Technology</i> , <b>1999</b> , 12, 901-903	3.1	5
67	Drastic Improvement in Surface Flatness Properties by Using GaAs (111)A Substrates in Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1999</b> , 38, 635-644	1.4	15
66	SEM imaging of fundamental growth processes during MBE of GaAs on (111)A substrates. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 124-127	1.6	2
65	First-principles calculations on atomic and electronic structures of misfit dislocations in InAs/GaAs(1 1 0) and GaAs/InAs(1 1 0) heteroepitaxies. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 256-259	1.6	8
64	Vertical transport properties through pseudo-metallic InAs thin films grown on GaAs (111)A substrates. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 778-781	1.6	
63	Microscopic investigation of the surface phase transition on GaAs(001) surfaces. <i>Surface Science</i> , <b>1999</b> , 433-435, 382-386	1.8	11
62	First-principles calculation for misfit dislocations in InAs/GaAs(110) heteroepitaxy. <i>Surface Science</i> , <b>1999</b> , 433-435, 900-903	1.8	9
61	Imaging of Local Charge Density in an InAs/GaAs Two-Dimensional Heterostructure by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, L899-L901	1.4	6
60	Imaging of layer by layer growth processes during molecular beam epitaxy of GaAs on (111)A substrates by scanning electron microscopy. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 3079-3081	3.4	21
59	Thickness-dependent electron accumulation in InAs thin films on GaAs(111)A: A scanning-tunneling-spectroscopy study. <i>Physical Review B</i> , <b>1998</b> , 58, R4219-R4222	3.3	32
58	Improvement in the Electrical Properties of GaAs/InAs/GaAs Structures through the Use of (111)A Substrates. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 1599-1602	1.4	15
57	Scanning Tunneling Microscopy Study of GaAs (001) Surfaces Grown by Migration-Enhanced Epitaxy at Low Temperatures. <i>Japanese Journal of Applied Physics</i> , <b>1998</b> , 37, 758-761	1.4	5
56	Scanning tunneling microscopy studies of strain relaxation and misfit dislocations in InAs layers grown on GaAs(110) and GaAs(111)A. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1997</b> , 15, 915-918	2.9	19
55	Extremely long surface diffusion of Ga and critical nucleation on As-rich GaAs(001) surfaces caused by phase transitions. <i>Physical Review B</i> , <b>1997</b> , 56, 12080-12083	3.3	35
54	Atomic-scale imaging of strain relaxation via misfit dislocations in highly mismatched semiconductor heteroepitaxy: InAs/GaAs(111)A. <i>Physical Review B</i> , <b>1997</b> , 55, 1337-1340	3.3	118



53	A Scanning Tunneling Microscopy-Reflection High Energy Electron Diffraction-Rate Equation Study of the Molecular Beam Epitaxial Growth of InAs on GaAs(001), (110) and (111)A Quantum Dots and Two-Dimensional Modes. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4111-4117	1.4	77
52	RHEED and STM study of the two-dimensional growth of InAs on GaAs (111)A. <i>Microelectronics Journal</i> , <b>1997</b> , 28, 825-831	1.8	2
51	Precise control of two dimensional growth of InAs on GaAs (111)A surfaces studied by scanning tunneling microscopy. <i>Applied Surface Science</i> , <b>1997</b> , 112, 138-141	6.7	2
50	In situ observation of MEE GaAs growth using scanning electron microscopy. <i>Journal of Crystal Growth</i> , <b>1997</b> , 175-176, 292-297	1.6	5
49	Electronic properties of monolayer steps on GaAs (0 0 1) surfaces studied by scanning tunneling microscopy. <i>Journal of Crystal Growth</i> , <b>1997</b> , 175-176, 304-309	1.6	1
48	Structure analysis of the GaAs(001)-2 × 4 surface using medium energy ion scattering. <i>Surface Science</i> , <b>1996</b> , 355, L361-L365	1.8	4
47	Reconstruction-dependent electron-hole recombination on GaAs(001) surfaces studied by using near-surface quantum wells. <i>Physical Review B</i> , <b>1996</b> , 53, 7880-7883	3.3	5
46	Electronic properties of monolayer steps on (2 × 4)/(2 × 8) reconstructed GaAs(001) surfaces. <i>Physical Review B</i> , <b>1996</b> , 54, 4428-4431	3.3	10
45	Direct comparison of GaAs surface morphology between migration enhanced epitaxy and molecular beam epitaxy using in situ scanning electron microscopy. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 63-65	3.4	25
44	Inhibitions of three dimensional island formation in InAs films grown on GaAs (111)A surface by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 776-778	3.4	103
43	Surface-defect formation on heavily doped InAs and GaAs layers studied by scanning tunneling microscopy. <i>Physical Review B</i> , <b>1996</b> , 53, 4565-4569	3.3	16
42	Direct determination of impact-parameter-dependent stopping powers for million-electron-volt He ions penetrating Er-doped GaAs. <i>Physical Review A</i> , <b>1996</b> , 53, 1644-1652	2.6	7
41	Effect of Growth Interruption during GaAs/AlGaAs Molecular Beam Epitaxy on (411)A Substrates. <i>Japanese Journal of Applied Physics</i> , <b>1996</b> , 35, L822-L824	1.4	3
40	Unified model for first-order transition and electrical properties of InAs (001) surfaces based on atom-resolved scanning tunneling microscopy imaging. <i>Journal of Crystal Growth</i> , <b>1995</b> , 150, 148-151	1.6	4
39	Effects of alloy composition on the As desorption from and adsorption on strained In <sub>x</sub> Ga <sub>1-x</sub> As surfaces. <i>Journal of Crystal Growth</i> , <b>1995</b> , 150, 473-477	1.6	1
38	Structural analysis of erbium sheet-doped GaAs grown by molecular-beam epitaxy, with ion channeling followed by Monte Carlo simulation. <i>Journal of Applied Physics</i> , <b>1995</b> , 77, 3095-3103	2.5	12
37	Indium desorption from InAs surfaces and its dependence on As coverage. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 3948-3950	3.4	5
36	In situ observation of phase transition and the transition-induced step bunching on InAs(001) surfaces by scanning electron microscopy. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1626-1628	3.4	2



35	Flattening Transition on GaAs (411)A Surfaces Observed by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1995</b> , 34, L1490-L1493	1.4	16
34	Surface structure transitions on InAs and GaAs (001) surfaces. <i>Physical Review B</i> , <b>1995</b> , 51, 9836-9854	3.3	92
33	Desorption and segregation of Indium and its dependence on surface As-coverage. <i>Materials Research Society Symposia Proceedings</i> , <b>1995</b> , 405, 31		
32	Unified Model for Structure Transition and Electrical Properties of InAs (001) Surfaces Studied by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, L1423-L1426	1.4	34
31	Step Motion and Structure Transition on InAs and GaAs (001) Surfaces Observed by Scanning Tunneling Microscopy. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, 716-720	1.4	13
30	Impact-parameter dependent stopping powers for axially channeled and semichanneled MeV He ions in GaAs:Er. <i>Physical Review B</i> , <b>1994</b> , 49, 14387-14396	3.3	14
29	Arsenic pressure dependence of first-order phase transition on InAs (001) surface. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 2572-2574	3.4	5
28	In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy. <i>Applied Surface Science</i> , <b>1994</b> , 82-83, 223-227	6.7	3
27	Dependence of ErAs Clustering and Er Segregation in ErAs/GaAs Heterostructures on Growth Temperature. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, L1784-L1787	1.4	15
26	Step motion and As desorption on InAs(001) surfaces observed by scanning tunneling microscopy. <i>Physical Review B</i> , <b>1993</b> , 48, 2807-2810	3.3	20
25	Scanning tunneling microscopy observation of monolayer steps on GaAs(001) vicinal surfaces grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 678-680	3.4	20
24	Influence of monomolecular steps on the first-order structure transition of an InAs(001) surface. <i>Physical Review Letters</i> , <b>1993</b> , 70, 1299-1302	7.4	33
23	Phase transition on III-V compound semiconductor surfaces observed by an improved RHEED technique. <i>Journal of Crystal Growth</i> , <b>1993</b> , 127, 976-980	1.6	6
22	Observation of GaAs (001) surfaces at high temperatures by scanning tunneling microscopy. <i>Journal of Crystal Growth</i> , <b>1993</b> , 127, 1064-1067	1.6	3
21	Surface Atomic Processes during Epitaxial Growth <b>1993</b> , 1-10		
20	First-order surface-structure transition on the (001) InAs surface studied with improved high-energy electron reflectivity measurements. <i>Physical Review B</i> , <b>1992</b> , 45, 1511-1513	3.3	22
19	As desorption from GaAs and AlAs surfaces studied by improved high-energy electron reflectivity measurements. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 1753-1759	2.5	15
18	Growth of GaAs/ErAs/GaAs structures by migration-enhanced epitaxy. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 2341-2343	3.4	17

17	As desorption from GaAs and InAs surfaces studied by improved high-energy electron reflectivity measurements. <i>Applied Surface Science</i> , <b>1992</b> , 60-61, 224-227	6.7	4
16	Influence of surface reconstruction on the As desorption process from a (001) GaAs surface evaluated by improved high-energy electron-reflectivity measurements. <i>Physical Review B</i> , <b>1991</b> , 44, 5897-5900	3.3	17
15	Influence of an As-Free Atmosphere in Migration-Enhanced Epitaxy on Step-Flow Growth. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, 802-808	1.4	17
14	Growth process of III-V compound semiconductors by migration-enhanced epitaxy. <i>Journal of Crystal Growth</i> , <b>1990</b> , 105, 326-338	1.6	141
13	Replacement of group-III atoms on the growing surface during migration-enhanced epitaxy. <i>Journal of Applied Physics</i> , <b>1990</b> , 68, 1610-1615	2.5	54
12	Anomalous Distribution of In Atoms in GaAs during Migration-Enhanced Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L2010-L2012	1.4	10
11	Step-Flow Growth on Vicinal GaAs Surfaces by Migration-Enhanced Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L1456-L1459	1.4	40
10	Surface Migration of Ga and Al Atoms on (100) GaAs and AlAs during Migration-Enhanced Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, 1307-1311	1.4	16
9	Luminescence Characteristics from Gaussian Shaped Quantum Wells. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L507-L509	1.4	3
8	Migration-enhanced epitaxy. <i>Applied Surface Science</i> , <b>1988</b> , 33-34, 406-412	6.7	8
7	Migration-Enhanced Epitaxy of GaAs and AlGaAs. <i>Japanese Journal of Applied Physics</i> , <b>1988</b> , 27, 169-179	1.4	331
6	Photoluminescence characteristics of AlGaAs-GaAs single quantum wells grown by migration-enhanced epitaxy at 300 °C substrate temperature. <i>Applied Physics Letters</i> , <b>1987</b> , 50, 1686-1687 <sup>4</sup>		47
5	N = 2 harmonic superspace with central charges and its application to self-interacting massive hypermultiplets. <i>Annals of Physics</i> , <b>1986</b> , 172, 26-39	2.5	9
4	Low-Temperature Growth of GaAs and AlAs-GaAs Quantum-Well Layers by Modified Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1986</b> , 25, L868-L870	1.4	358
3	Superfield perturbation theory in harmonic superspace. <i>Physical Review D</i> , <b>1985</b> , 32, 1954-1967	4.9	11
2	Dipole mechanism of spontaneous breaking of N=2 supersymmetry: Violation of positivity bound on central charges. <i>Physical Review D</i> , <b>1984</b> , 30, 2181-2188	4.9	3
1	Fabrication of Nanomechanical Structures from Bulk-GaAs Using Angled Ion Etching. <i>Applied Physics Express</i> , <b>2</b> , 065001	2.4	4